

ABSTRACT

The present invention provides a reflective mask blank and reflective mask capable of reducing the shadowing effect of EUV lithography and forming a fine pattern.

5 As a result, a semiconductor device can be more stably manufactured with high transfer accuracy. The reflective mask blank comprises a multilayer reflective film, an absorber film and an etching mask film on a substrate in that order, wherein the absorber film is made of a material containing nickel (Ni), and the etching mask film is made of a material containing chromium (Cr) or a material containing silicon (Si).

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